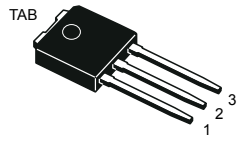
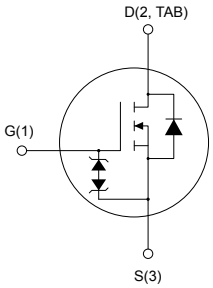
STU2NK100Z

Datasheet

N-channel 1000 V, 6.25 Ω typ., 1.85 A SuperMESH Power MOSFET in an IPAK package



IPAK



AM01476v1_tab

Features

Order code	V_{DS}	$R_{DS(on)}$ max.	I_D
STU2NK100Z	1000 V	8.5 Ω	1.85 A

- 100% avalanche tested
- Gate charge minimized
- Very low intrinsic capacitance
- Zener-protected

Applications

- Switching applications

Description

This high-voltage device is a Zener-protected N-channel Power MOSFET developed using the SuperMESH technology by STMicroelectronics, an optimization of the well-established PowerMESH. In addition to a significant reduction in on-resistance, this device is designed to ensure a high level of dv/dt capability for the most demanding applications.

Product status link
STU2NK100Z

Product summary	
Order code	STU2NK100Z
Marking	2NK100Z
Package	IPAK
Packing	Tube

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	1000	V
V_{GS}	Gate-source voltage	±30	V
I_D	Drain current (continuous) at T_C = 25 °C	1.85	A
	Drain current (continuous) at T_C = 100 °C	1.6	
I_{DM}(1)	Drain current (pulsed)	7.4	A
P_{TOT}	Total power dissipation at T_C = 25 °C	70	W
ESD	Gate-source, human body model (R = 1.5 kΩ, C = 100 pF)	3	kV
dv/dt(2)	Peak diode recovery voltage slope	2.5	V/ns
T_{stg}	Storage temperature range	-55 to 150	°C
T_J	Operating junction temperature range		°C

1. *Pulse width limited by safe operating area.*
2. *I_{SD} ≤ 1.85 A, di/dt ≤ 200 A/µs, V_{DD} = 80% $V_{(BR)DSS}$.*

Table 2. Thermal data

Symbol	Parameter	Value	Unit
R_{thJC}	Thermal resistance, junction-to-case	1.79	°C/W
R_{thJA}	Thermal resistance, junction-to-ambient	100	°C/W

Table 3. Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetitive or not repetitive (pulse width is limited by T_J max.)	1.85	A
E_{AS}	Single pulse avalanche energy (starting T_J = 25 °C, I_D = I_{AR}, V_{DD} = 50 V)	170	mJ

2 Electrical characteristics

T_C = 25 °C unless otherwise specified.

Table 4. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	V_{GS} = 0 V, I_D = 1 mA	1000			V
I_{DSS}	Zero gate voltage drain current	V_{GS} = 0 V, V_{DS} = 1000 V			1	µA
		V_{GS} = 0 V, V_{DS} = 1000 V, T_C = 125 °C(1)			50	µA
I_{GSS}	Gate-body leakage current	V_{DS} = 0 V, V_{GS} = ±30 V			±10	µA
$V_{GS(th)}$	Gate threshold voltage	V_{DS} = V_{GS}, I_D = 50 µA	3	3.75	4.5	V
$R_{DS(on)}$	Static drain-source on resistance	V_{GS} = 10 V, I_D = 0.9 A		6.25	8.5	Ω

1. *Specified by design, not tested in production.*

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	V_{DS} = 25 V, f = 1 MHz, V_{GS} = 0 V	-	499	-	pF
C_{oss}	Output capacitance		-	53	-	pF
C_{rss}	Reverse transfer capacitance		-	9	-	pF
$C_{oss\ eq.}$ (1)	Equivalent output capacitance	V_{GS} = 0 V, V_{DS} = 0 V to 800 V	-	28	-	pF
R_G	Gate input resistance	f = 1 MHz, open drain	-	6.6	-	Ω
Q_g	Total gate charge	V_{DD} = 800 V, I_D = 1.85 A, V_{GS} = 0 to 10 V (see Figure 14. Test circuit for gate charge behavior)	-	16	-	nC
Q_{gs}	Gate-source charge		-	3	-	nC
Q_{gd}	Gate-drain charge		-	9	-	nC

1. *$C_{oss\ eq.}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS}increases from 0 to 80% V_{DSS}.*

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	V_{DD} = 500 V, I_D = 0.9 A, R_G = 4.7 Ω, V_{GS} = 10 V (see Figure 13. Test circuit for resistive load switching times and Figure 18. Switching time waveform)	-	7.2	-	ns
t_r	Rise time		-	6.5	-	ns
$t_{d(off)}$	Turn-off delay time		-	41.5	-	ns
t_r	Fall time		-	32.5	-	ns

Table 7. Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		1.85	A
I_{SDM} (1)	Source-drain current (pulsed)		-		7.4	A
V_{SD} (2)	Forward on voltage	I_{SD} = 1.85 A, V_{GS} = 0 V	-		1.6	V
t_{rr}	Reverse recovery time	I_{SD} = 1.85 A, di/dt = 100 A/µs	-	476		ns
Q_{rr}	Reverse recovery charge	V_{DD} = 60 V	-	1.6		µC
I_{RRM}	Reverse recovery current	(see Figure 15. Test circuit for inductive load switching and diode recovery times)	-	6.9		A
t_{rr}	Reverse recovery time	I_{SD} = 1.85 A, di/dt = 100 A/µs	-	532		ns
Q_{rr}	Reverse recovery charge	V_{DD} = 60 V, T_J = 150 °C	-	1.9		µC
I_{RRM}	Reverse recovery current	(see Figure 15. Test circuit for inductive load switching and diode recovery times)	-	88		A

1. *Pulse width is limited by safe operating area.*
2. *Pulsed: pulse duration = 300 µs, duty cycle 1.5%.*

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

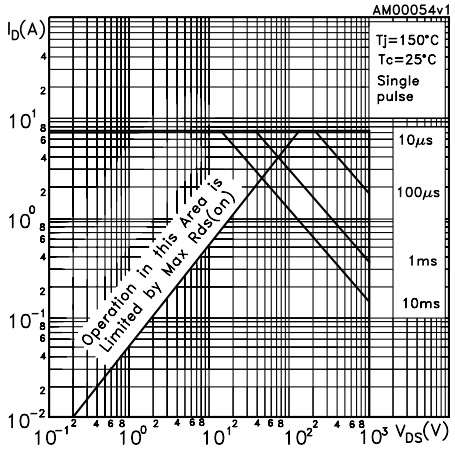


Figure 2. Thermal impedance

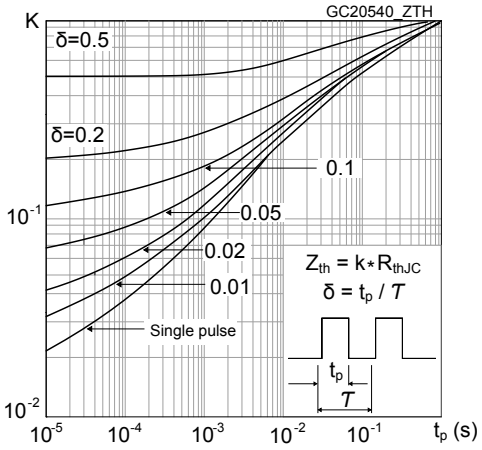


Figure 3. Output characterisics

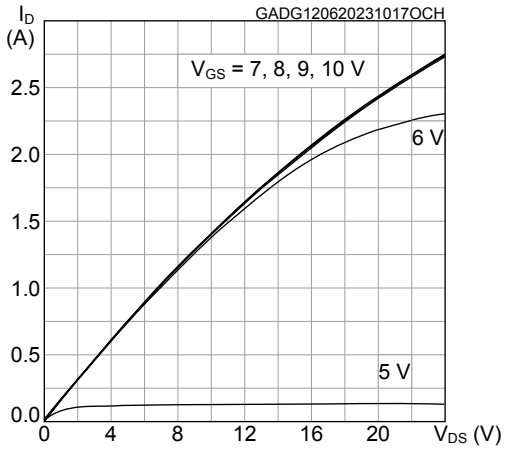


Figure 4. Transfer characteristics

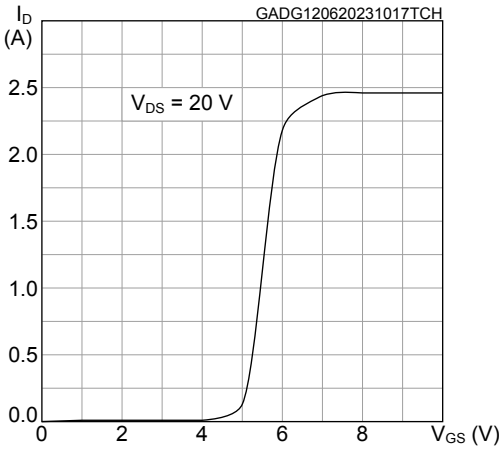


Figure 5. Normalized $V_{(BR)DSS}$ vs temperature

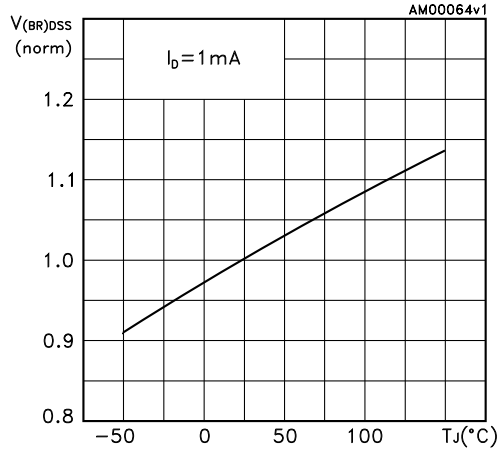


Figure 6. Static drain-source on resistance

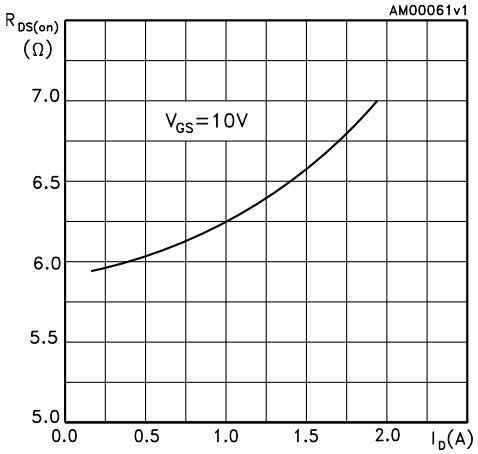


Figure 7. Gate charge vs gate-source voltage

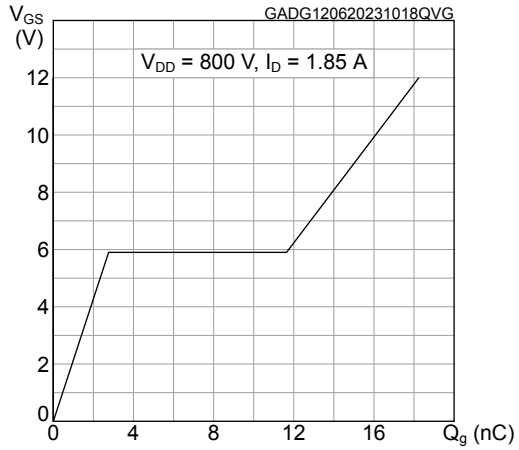


Figure 8. Capacitance variations

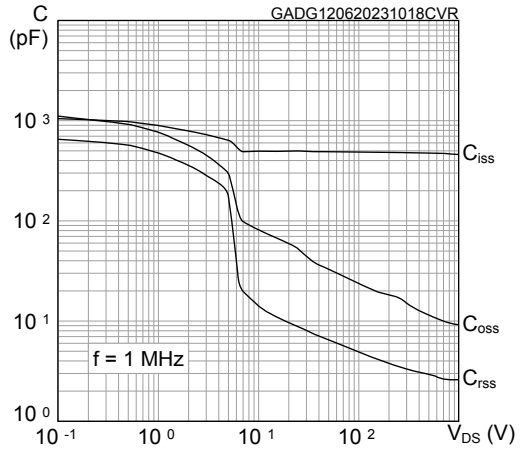


Figure 9. Normalized gate threshold voltage vs temperature

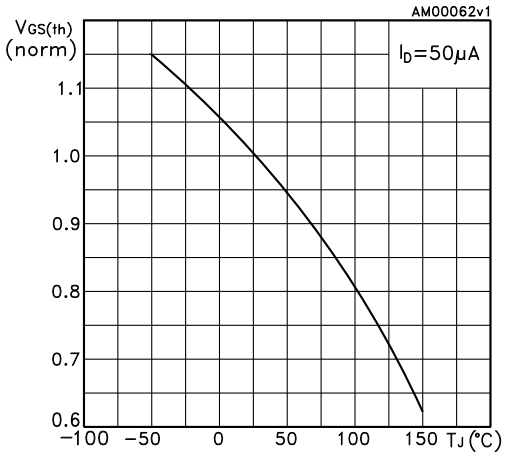


Figure 10. Normalized on resistance vs temperature

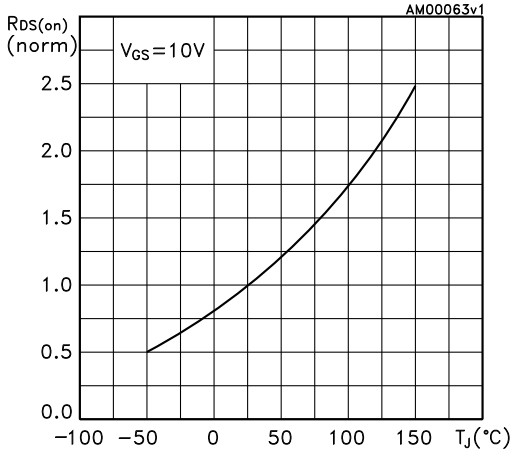


Figure 11. Source-drain diode forward characteristics

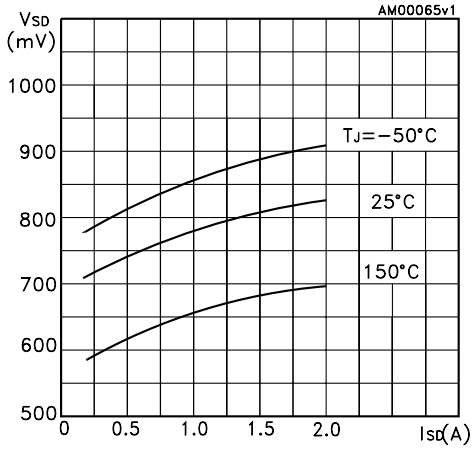
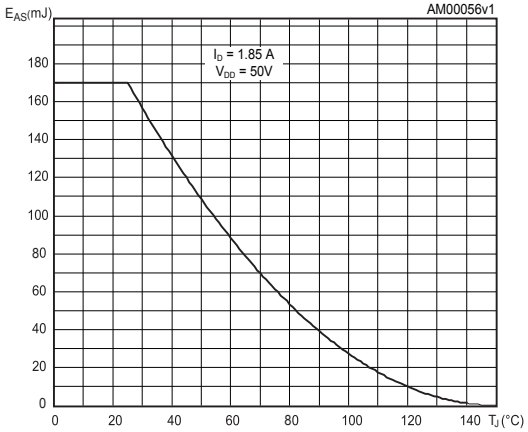
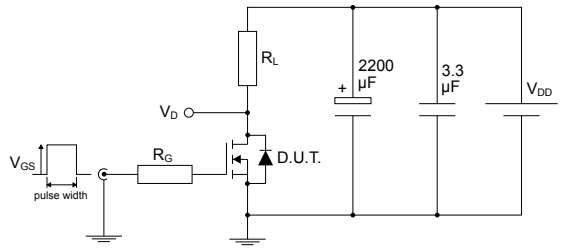


Figure 12. Maximum avalanche energy vs temperature



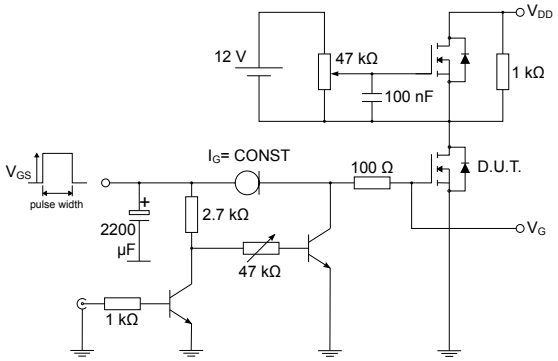
3 Test circuits

Figure 13. Test circuit for resistive load switching times



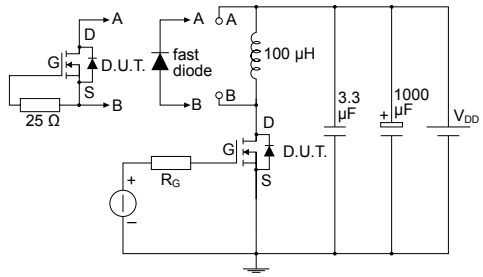
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Figure 14. Test circuit for gate charge behavior



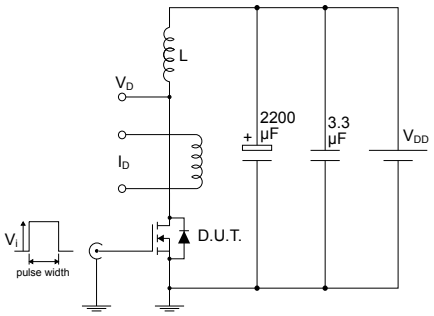
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Figure 15. Test circuit for inductive load switching and diode recovery times



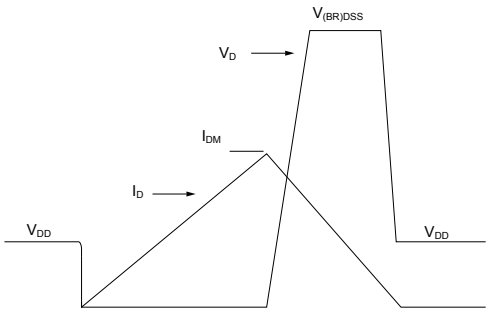
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Figure 16. Unclamped inductive load test circuit



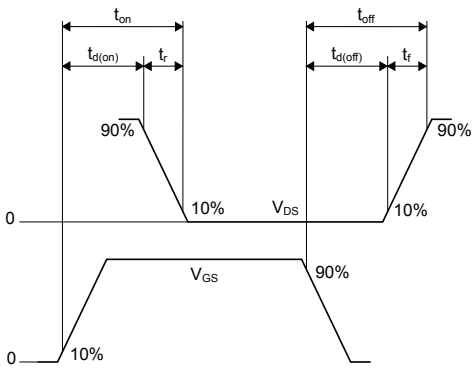
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Figure 17. Unclamped inductive waveform



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Figure 18. Switching time waveform



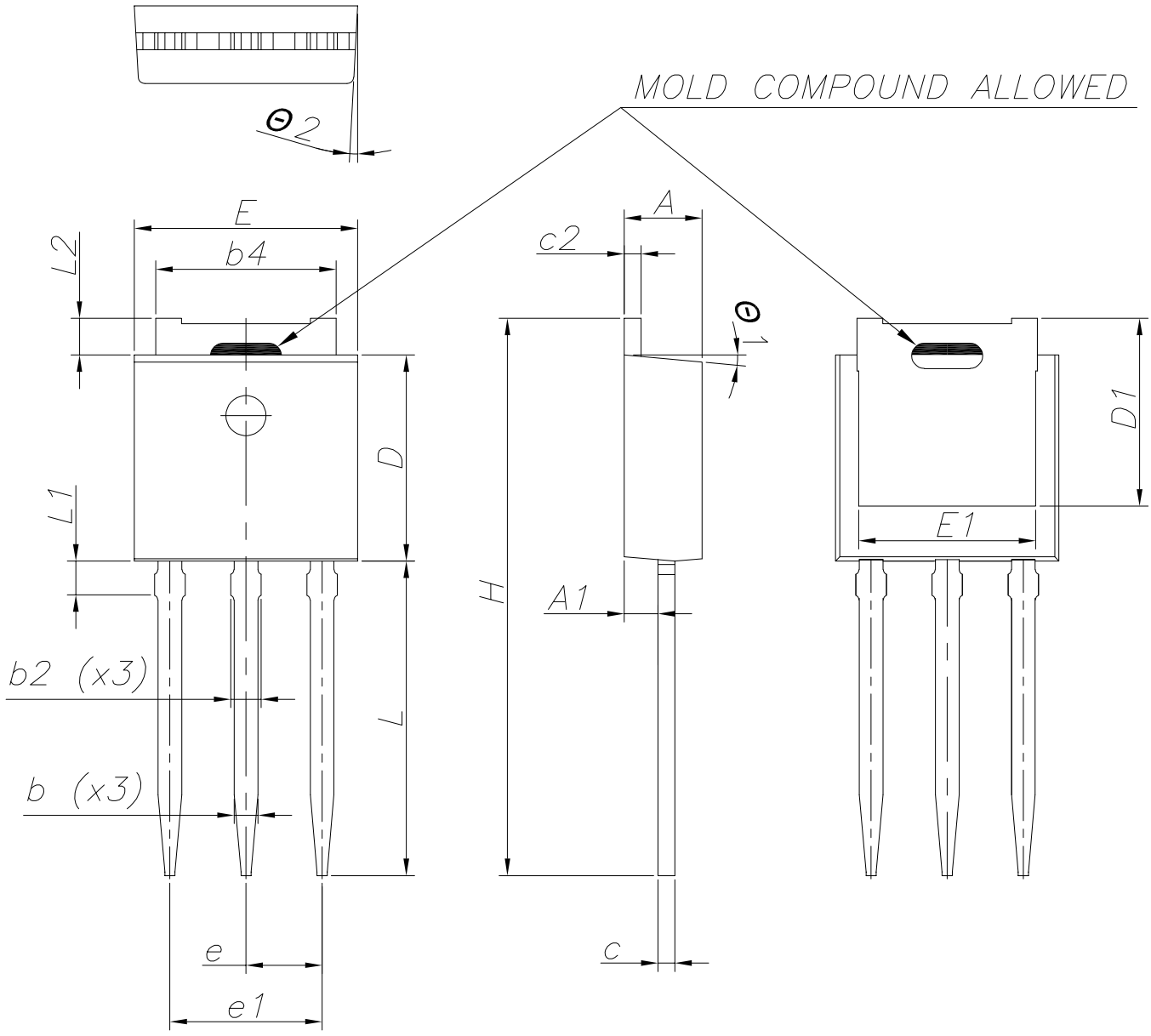
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4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

4.1 IPAK (TO-251) type E package information

Figure 19. IPAK (TO-251) type E package outline



0068771_E_rev.16

Table 8. **IPAK (TO-251) type E package mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	2.20	2.30	2.35
A1	0.90	1.00	1.10
b	0.66		0.79
b2			0.90
b4	5.23	5.33	5.43
c	0.46		0.59
c2	0.46		0.59
D	6.00	6.10	6.20
D1	5.30	5.53	5.75
E	6.50	6.60	6.70
E1	5.05	5.23	5.40
e	2.20	2.25	2.30
e1	4.40	4.50	4.60
H	16.18	16.48	16.78
L	9.00	9.30	9.60
L1	0.80	1.00	1.20
L2	0.90	1.08	1.25
Θ1	3°	5°	7°
Θ2	1°	3°	5°

Revision history

Table 9. **Document revision history**

Date	Revision	Changes
24-Oct-2007	1	First release
18-Jun-2008	2	– Inserted new package, mechanical data IPAK – Document status promoted from preliminary data to datasheet.
28-Jun-2018	3	Removed maturity status indication from cover page. The document status is production data. Updated title in cover page, *Section 1 Electrical ratings*, *Section 2 Electrical characteristics* and *Section 4 Package information*. Minor text changes.
15-Jun-2023	4	The part numbers STD2NK100Z and STP2NK100Z have been moved to a separate datasheet and the document has been updated accordingly. Removed "*Table 8. Gate-source Zener diode*". Updated Figure 3. Output characterisics, Figure 4. Transfer characteristics, Figure 7. Gate charge vs gate-source voltage and Figure 8. Capacitance variations. Removed "*Section 4.5 IPAK (TO-251) type A package information*" and added Section 4.1 IPAK (TO-251) type E package information. Minor text changes.

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